# **BLP25M705**

# **Broadband LDMOS driver transistor**

Rev. 1 — 15 August 2013

**Product data sheet** 

### 1. Product profile

### 1.1 General description

A 5 W LDMOS power transistor for broadcast and industrial applications in the HF to 2500 MHz band.

Table 1. Application information

Test signal	f	I <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L</sub>	Gp	η <sub>D</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)
Pulsed RF [1]	2450	50	28	5	15.8	41.4

<sup>[1]</sup> Measured at  $\delta$  = 10 %,  $t_p$  = 12  $\mu s.$ 

### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- High power gain
- Designed for broadband operation (HF to 2500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



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# 2. Pinning information

Table 2. Pinning

Table 2. I Illining			
Pin	Description	Simplified outline	Graphic symbol
1, 4, 5, 6, 7, 8, 9, 12	n.c.	40 7	40.44
2, 3	gate	12 7	10, 11
10, 11	drain		2, 3
13	source	[1]	13
		<u> </u>	aaa-007870
		Transparent top view	

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLP25M705	HVSON12	plastic thermal enhanced very thin small outline package; no leads; 12 terminals; body $6 \times 4 \times 0.85$ mm	SOT1179-2			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C

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## 5. Recommended operating conditions

See application note AN11198 for more details.

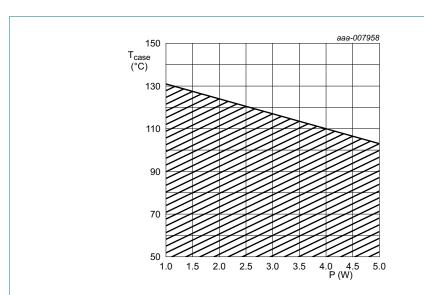


Fig 1. Recommended operating area; case temperature as a function of power dissipation

### 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80  ^{\circ}C;  P_{L} = 5  W$	[1] 6.4	K/W

<sup>[1]</sup>  $R_{th(j-c)}$  is measured under RF conditions.

### 7. Characteristics

Table 6. DC characteristics

 $T_j = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.09 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 9 \text{ mA}$	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 55 \text{ mA}$	1.45	2.0	2.55	V
$I_{\text{DSS}}$	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	1.6	-	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_{D} = 9 \text{ mA}$	-	80	-	mS
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 315 \text{ mA}$	-	2	-	Ω

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Table 7. RF characteristics

Test signal: 1-tone pulsed;  $t_p$  = 50  $\mu$ s;  $\delta$  = 10 %; f = 2140 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 55 mA;  $T_{case}$  = 25  $^{\circ}$ C; unless otherwise specified, in a production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$G_p$	power gain	$P_{L(AV)} = 1 W$	15	16	-	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 1 W$	20	23	-	%
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		5.5	-	-	W
RLin	input return loss	$P_{L(AV)} = 1 W$	-	-16	-12	dB

### 8. Test information

### 8.1 Ruggedness in class-AB operation

The BLP25M705 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 55 mA;  $P_{L}$  = 5 W (CW).

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## 9. Package outline

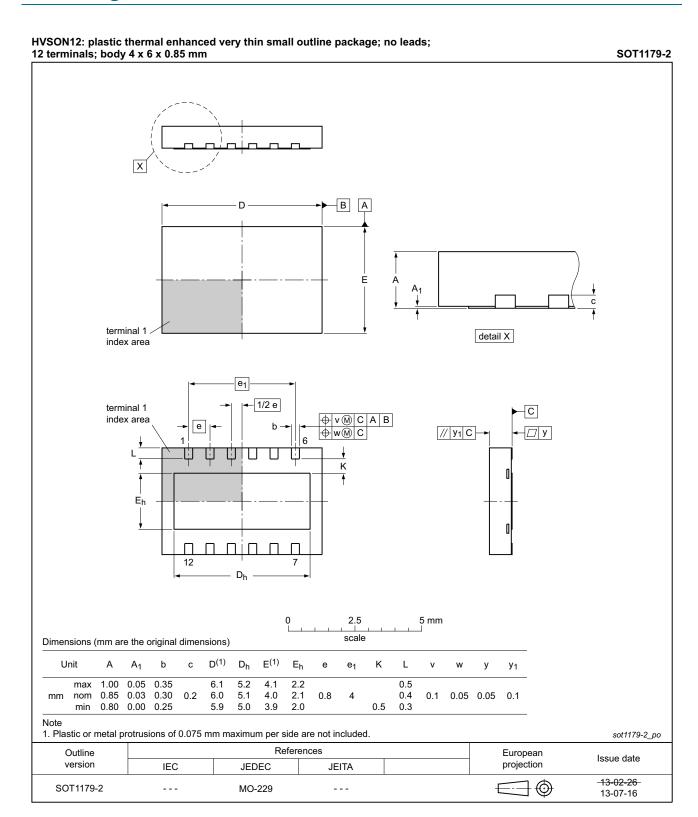


Fig 2. Package outline SOT1179-2 (HVSON12)

### **Broadband LDMOS driver transistor**

# 10. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 11. Abbreviations

Table 8. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
VSWR	Voltage Standing-Wave Ratio

## 12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP25M705 v.1	20130815	Product data sheet	-	-

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### 13. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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